

# **352-MHz RF Power System Development at the Advanced Photon Source**

Doug Horan – Advanced Photon Source RF Group 2010 – Sixth CW and High Average Power RF Workshop ALBA, Barcelona, Spain



# Present 350-MHz RF System Devices and Configuration

- Five 1.1MW CW rf stations provide power to the APS accelerators:
- → Each rf station utilizes one super-power klystron as a final amplifier
- → One rf station powers booster, four power storage ring
- → Each klystron requires a dc input power of ~ 90kV @ 20A dc to provide full output
- → Klystrons are cooled by 450 GPM of DI water at 90°F supply temperature
- → Typical rf output power for storage ring rf stations is
   ~ 600-700kW CW at this time

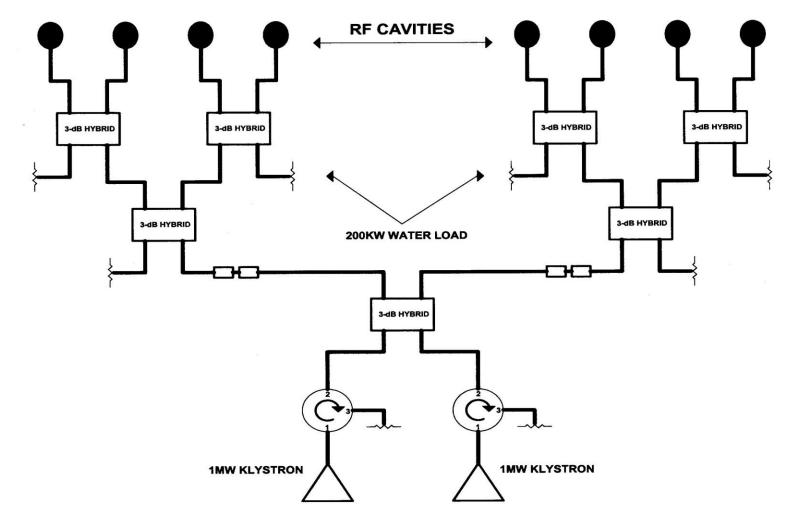


352-MHz/1.1MW CW klystron inside x-ray shield enclosure

*Typical rf system downtime is ~ 0.05 - 0.2%* 

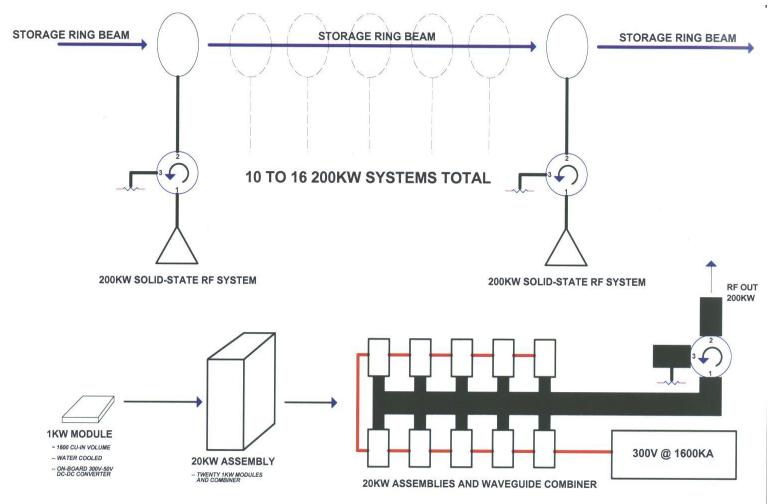
#### Present 350-MHz RF System Devices and Configuration

• The sixteen storage ring rf cavities are supplied rf power in two groups of eight, by either one klystron single-ended or two klystrons in parallel:



#### **Proposed 350-MHz Solid-State RF System Configuration**

The ultimate goal  $\rightarrow$  A 200kW CW solid-state rf system utilizing combined 1kW modules:



#### Some 1kW Module Design Challenges

- Greater than 99% reliability!
  - $\rightarrow$  One device per kilowatt or two?
  - $\rightarrow$  Thermal issues:
    - -- Is 1kW right at the limit of transistor package?
    - -- Cooling of board and passive components
- Development of on-board 1kW circulator and load
   → May get from industry, but at what cost for initial units?
- Primary input power:
  - → <u>On-board DC-to-DC converter</u>, or <u>480VAC to each</u> <u>module</u>?
  - → Design of 300V/50V dc-dc converter.....buy from industry or design in-house?

#### <u>APS 352-MHz/4kW Combined-Amplifier</u> <u>Solid-State Demonstration Project</u>

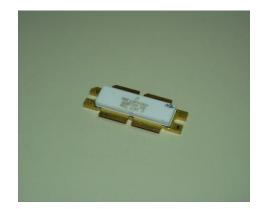
- Goal and Purpose:
  - → Demonstrate a 352-MHz 4kW CW combined solid-state amplifier system
  - → Determine practical power output limit from single part
  - → Produce baseline data to estimate the feasibility, cost, and MTTF of a 200kW combined-amplifier system
- Duration:

#### → Two years, FY09-FY10

#### **Proposed Design Features of 1kW Module**

- Capable of 1kW CW continuous output at 351.93MHz
- Operating bandwidth = 1MHz
- Gain = 30dB
- Linearity  $\rightarrow$  3rd order IMD -25dBc or greater
- Efficiency = 55% minimum
- Load Sensitivity → Able to operate at maximum power output at full reflection at all phase angles without damage
- Water cooled with existing de-ionized water system
- Internal 300V/50V DC-DC converter
- Internal 1kW circulator with load
- Volume ~ 1600 cubic inches (?)
- Capable of being removed from system with power applied
- Smart control system with diagnostic capabilities
- 99% reliability required

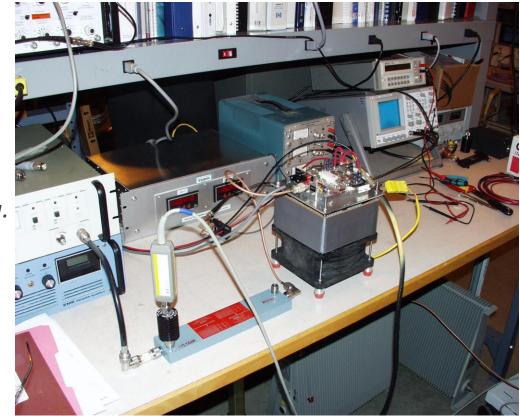
- Published ratings for the LDMOS push-pull transistor were for pulsed service:
   1kW peak,100us pulse, 20% duty factor.....
- We obtained a 450-MHz
   evaluation board kit from
   Freescale and tested it at
   rated power.





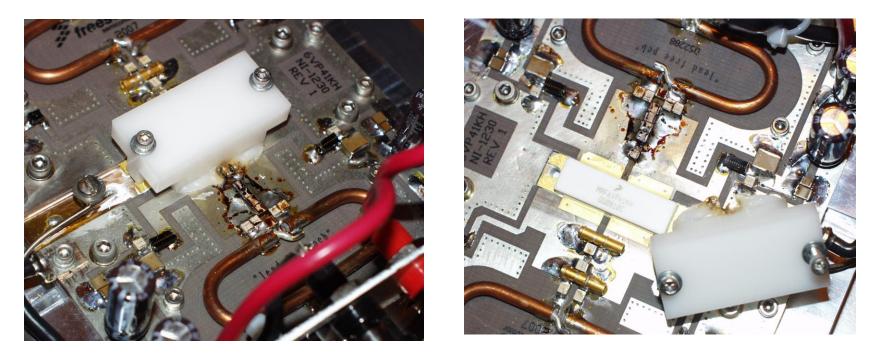
- The evaluation board produced 1kW peak power at 450MHz, 100us, 20%DF with no problems!
- I increased pulse width to 50% DF and the amplifier survived......
   → but passive components in
  - output network were overheating.

8/12/08 -Unexcased power by 1 dt ----HS Temp= 46°C PIN= 12.50 I dram = 34A peak on Hall meter Uncreased power to 1 Ku! HS Jomp - + 46.4°c 10000 pulse - 20% OF Po= 1.01Kupeak PIN= 14.5W Dear F= 450.0 Mlks



Amplifier test setup showing Forced-air cooling of "pin fin" heat sink

- Operation at 50% DF ended after approximately 10 minutes when the transistor was destroyed because of arcing on the drain leads.
- Excessive circuit board temperatures melted the delrin clamp that was holding the transistor drain leads to the circuit board foils.

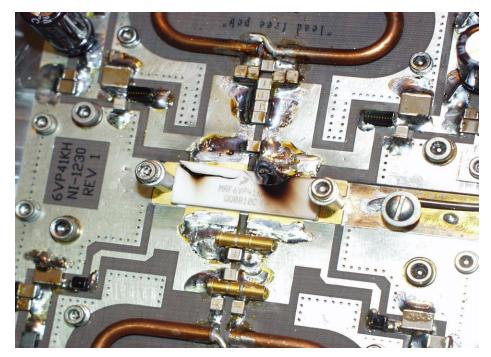


- The transistor was replaced and the leads were soldered to the board foils to eliminate the need for the delrin clamp.
- Operation at 1kW / 50% duty factor was successful.
- CW power was attempted, but the transistor failed after approximately seven seconds at ~ 400 watts CW output.

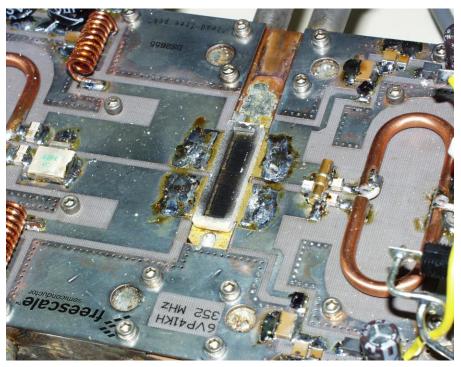
#### **CONCLUSION:**

→ Efficient water cooling should allow CW operation

→ Will cooling with 90°F water be acceptable?



- Freescale tested the MRF6VP41KHR6 device using a water-cooled copper cold plate and demonstrated 1kW CW output power at 352.21MHz
- We obtained two Freescale MRF6VP41KHR6 352.21MHz/1kW evaluation boards and assembled two amplifiers using "de-lidded" transistors supplied by Freescale
- We designed an improved copper cold plate for higher thermal efficiency.

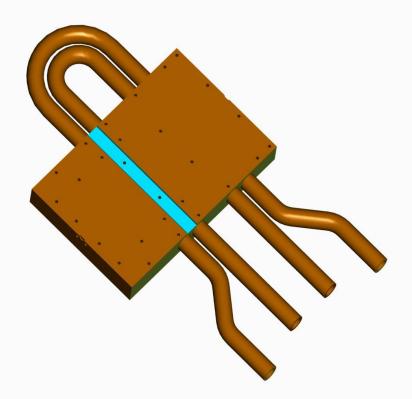


352-MHz Solid State RF Power System Development at APS -- 2010 CWRF Workshop May 4-7, 2010

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#### FY09 352-MHz 1kW CW Amplifier Test Plan

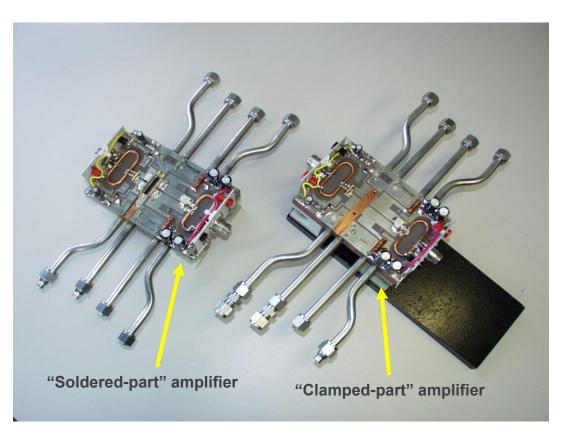
- Two Freescale 352-MHz/1kW
   CW water-cooled MRF6VP41KHR6 test amplifiers were built:
  - → One with soldered part
  - $\rightarrow$  One with clamped part
- Improved APS cold-plate design was utilized
- We directly measured transistor die temperature to arrive at the estimated MTTF for a combination of:
  - → Transistor mounting techniques
  - → Thermal performance of "carrier" design



#### Modified APS cold-plate design

• Construction of the amplifiers was difficult due to the thermal capacity of the copper cold plate.

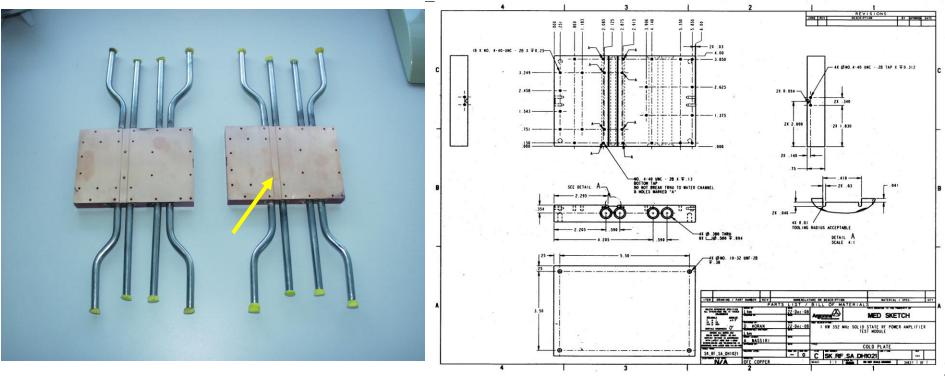
- → Assembly soldering had to be done in stages using a hot plate and a 200-watt soldering iron
- → Assembly was performed in stages using two solder alloys with different melting points



#### **Completed amplifiers**

#### Improved APS Cold Plate Design

• APS developed an improved copper cold plate design to maximize cooling efficiency for the transistor package and output circuit passive components:



→ "Clamped-part" cold plate has 4-40 threaded holes to attach the transistor to the cold plate

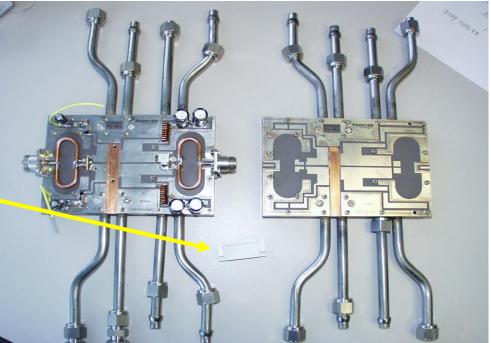
 $\rightarrow$  "Soldered-part" cold plate has no transistor mounting holes.....transistor is

soldered directly onto the cold Rplate May 4-7, 2010

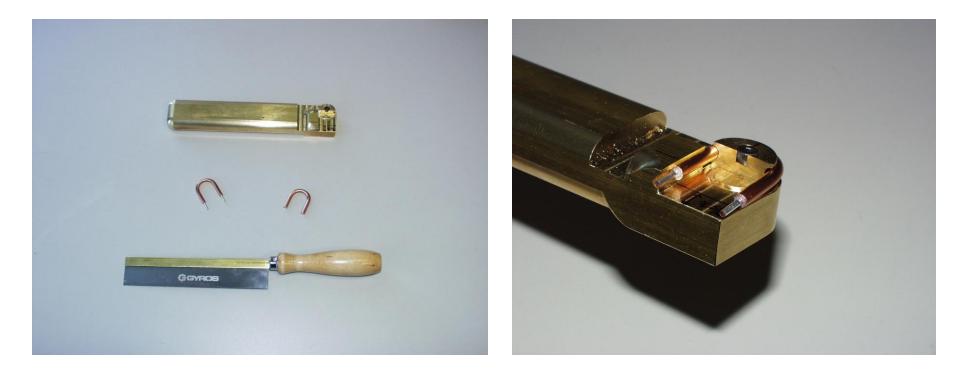
- The cold plates were tinned with 95%Sn/5%Sb solder with a melting point at ~ 240°C
- The circuit board was then soldered to the cold plate and pressed with a weight to insure uniform bonding.
  - → Insures good thermal and electrical contact between the circuit board and cold plate
  - → Uniform good electrical contact on back side of board is necessary for operating stability



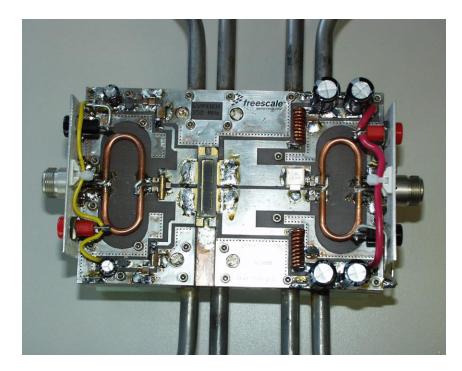
- On the clamped-part amplifier, passive components were soldered to the board foils that were thermally isolated from board ground and cold plate using one (and sometimes two!) 60-watt soldering irons.
- On the soldered-part amplifier, the transistor was soldered directly to the cold plate using regular 65%Sn/35%Pb solder with a melting point of approximately 183°C.
  - → A hold-down clamp was made from machineable ceramic to apply a small amount of weight to the transistor when it was soldered to the cold plate

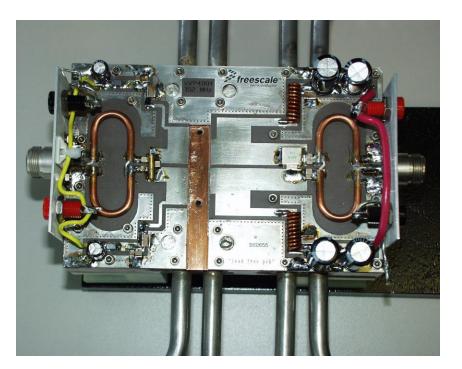


- Special saw (60 teeth/inch, 0.008" thickness) was utilized to cut the 25Ω rigid mini-coax for the input and output baluns
- A bending tool was fabricated to form the coaxial baluns.



 The remaining assembly was completed by heating the entire assembly to 120°C on the hot plate and using a 200-watt soldering iron to solder all connections that were thermally bonded to the cold plate.





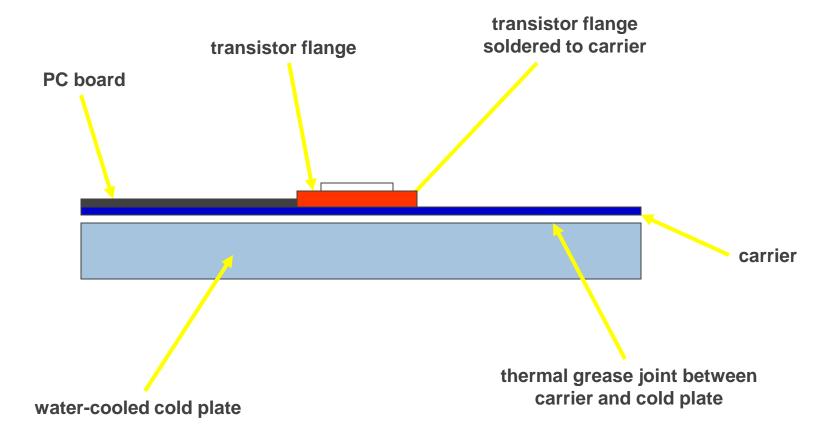
#### 352-MHz 1kW CW Amplifier Test System and Plan

- 75°F DI water supply for cooling amplifier
- Flow and supply/return temperature monitored on each water circuit
- IR camera for monitoring and recording transistor die temperatures on delidded transistors



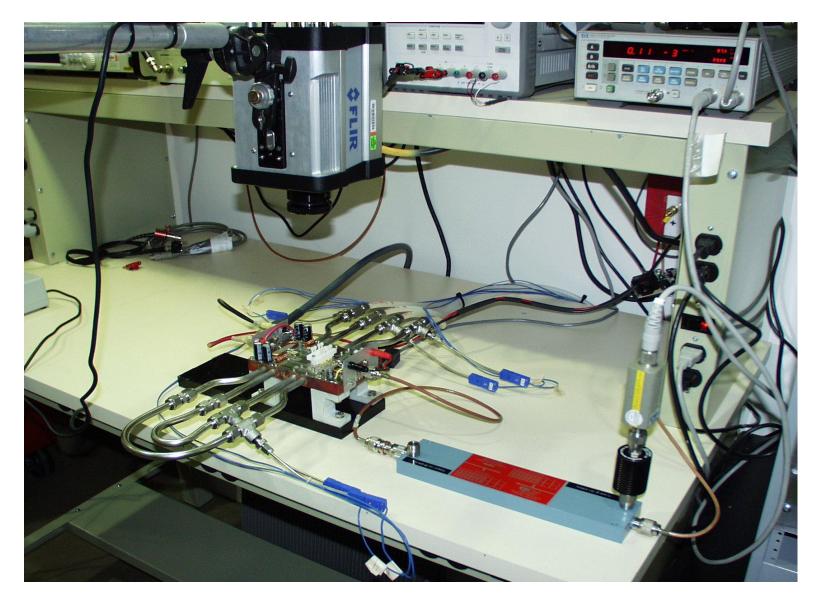
#### Lessons Learned from Test Results

• The use of a part "carrier" will make assembly much easier by allowing normal soldering techniques



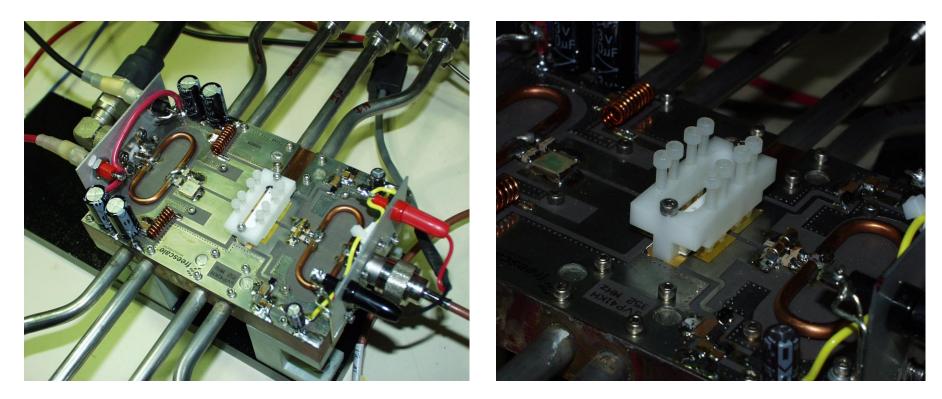
#### Carrier thickness of 4-6 mm will provide adequate thermal performance

#### 352-MHz 1kW CW Amplifier Test System and Plan



## 352-MHz 1kW CW Amplifier Test System and Plan

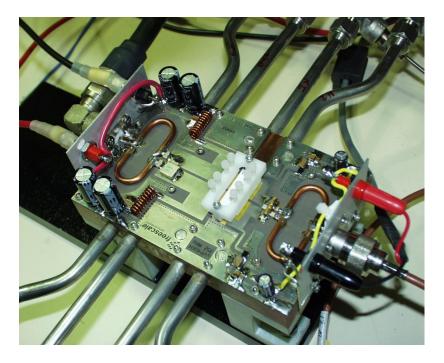
- The "clamped-part" amplifier uses a delrin clamp to mount the transistor to the cold plate, using a screw torque of 5 in-lbs.
- The delrin clamp holds transistor leads to board allowing for removal without damaging board.



#### 352-MHz 1kW CW "Clamped Part" Amplifier Test Results

- Clamped-part amplifier test results:
  - → Vd = 49.46V
  - → Id = 29.06A
  - → Idq ≈ 150mA
  - → Pdc input = 1437.3 watts
  - → Efficiency = 63.2%
  - → RF output ≈ 909 watts (derived from water calorimetric power calculations)
  - $\rightarrow$  RF input = 8.53 watts
  - →Input return loss = 10.3dB
  - →RF gain  $\approx$  20.2dB

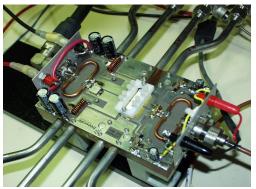
→Water calorimetric power = 528 watts

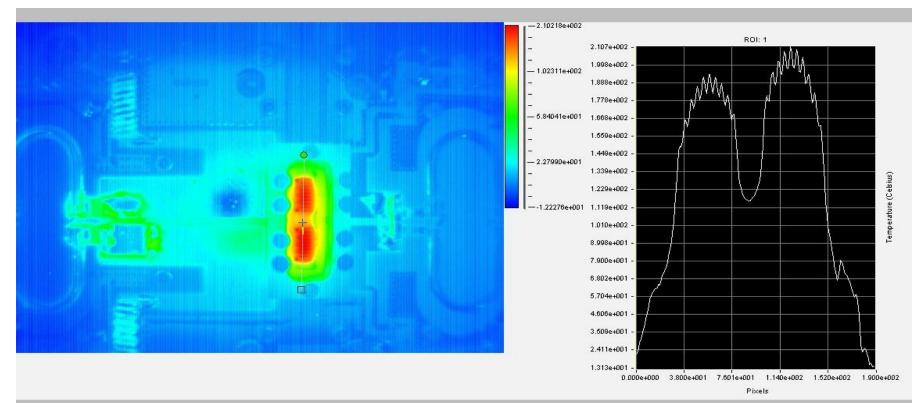


Initial efficiency was abnormally high (69.5%), so rf power meter readout at 1kW was suspect.....rf power was derived from power dissipation in water circuits

#### 352-MHz 1kW CW "Clamped Part" Amplifier Test Results

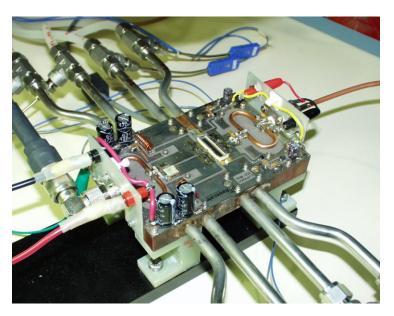
- Maximum die temperature was 210°C at ~ 909 watts output – excessive for reasonable device MTTF
- Test results agree with Freescale predictions for a clamped part

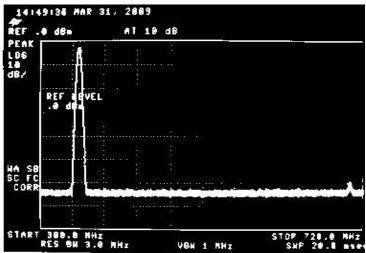




#### 352-MHz 1kW CW "Soldered Part" Amplifier Test Results

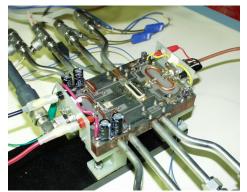
- Soldered-part amplifier test results:
  - → Vd = 49.26V
  - → Id = 30.65A
  - → Idq ≈ 150mA
  - → Pdc input = 1509.82 watts
  - → Efficiency = 66.2%
  - $\rightarrow$  RF output = 1000 watts
  - $\rightarrow$  RF input = 8.32 watts
  - → Input return loss = 10.07dB
  - → RF gain = 20.79dB
  - → Water calorimetric power = 572.8 watts

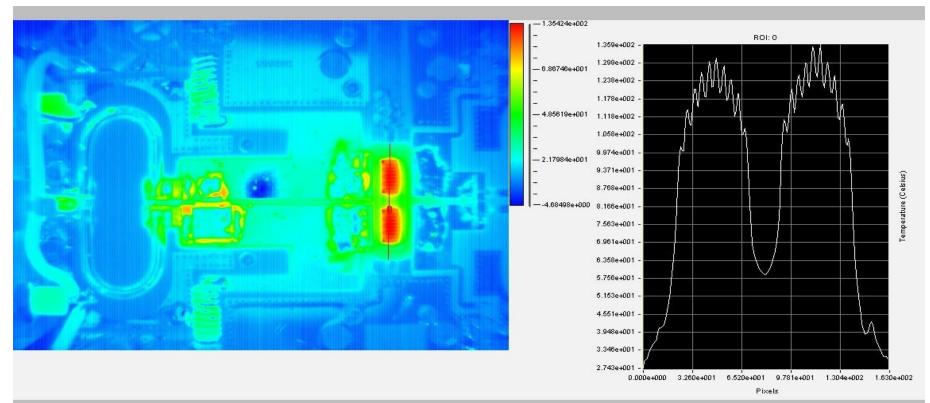




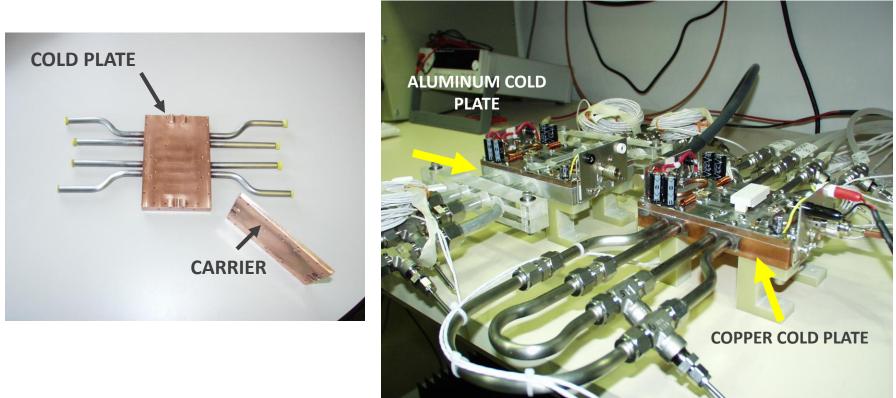
#### 352-MHz 1kW CW "Soldered Part" Amplifier Test Results

- Maximum die temperature was 136°C at 1kW output translates to a device MTTF of ~ 9E+6 hours.
- Temperature on top of flange between dies ~ 58°C
- As expected, the soldered-part construction technique offers more efficient cooling of device.





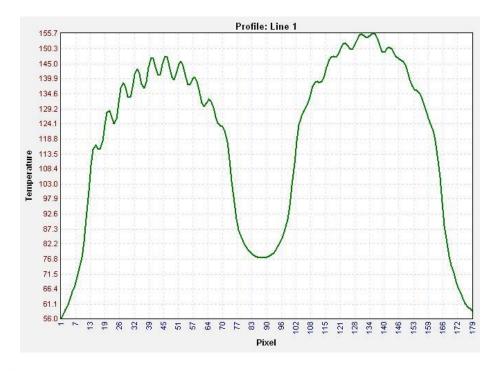
#### **Construction of "Carrier-Cold Plate" Amplifiers**

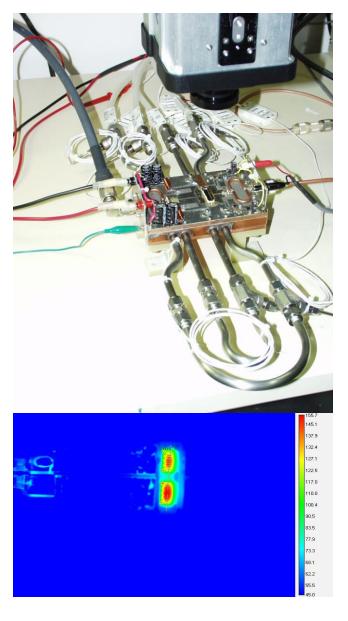


- Amplifier circuit board soldered to 0.25" carrier
- Carrier attached to cold plate by screws, using thermal grease for heat transfer
- Aluminum and copper cold plate built and tested

#### **Testing of Copper Cold Plate Amplifier**

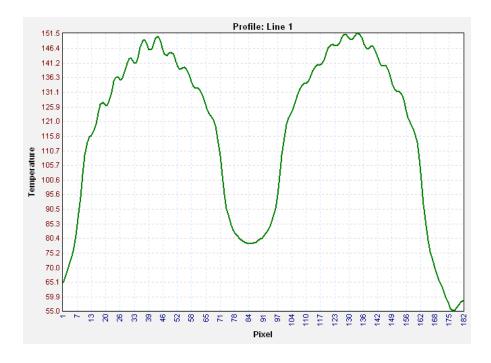
- Maximum die temperature at 1,012 watts output was 155.7 C
- 69.6% efficiency

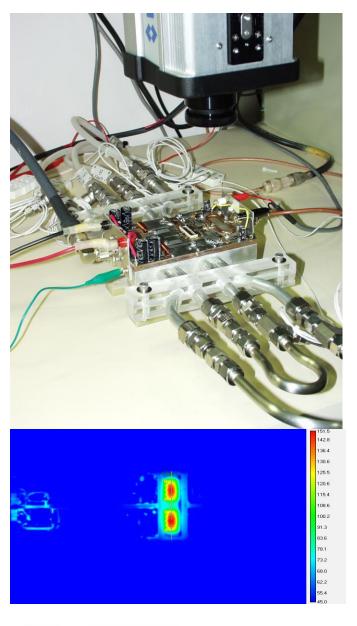




#### **Testing of Aluminum Cold Plate Amplifier**

- Maximum die temperature at 1,010 watts output was 151.5°C
- 69.6% efficiency





#### Thermal Performance of Aluminum and Copper Cold Plates

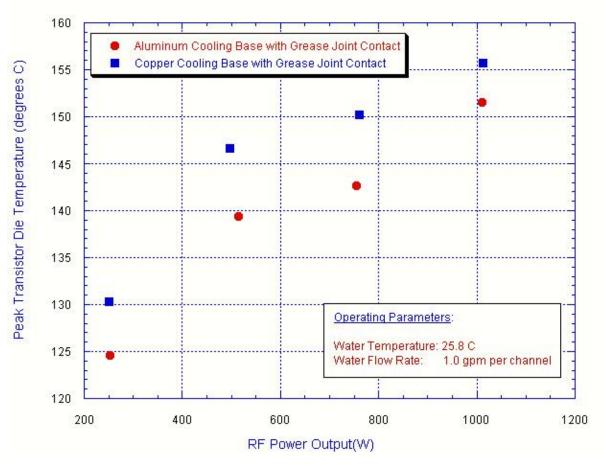
#### Freescale RF Amplifier Tests

Aluminum & Copper Cooling Bases with Grease Joint Contact

JTC 3/19/10

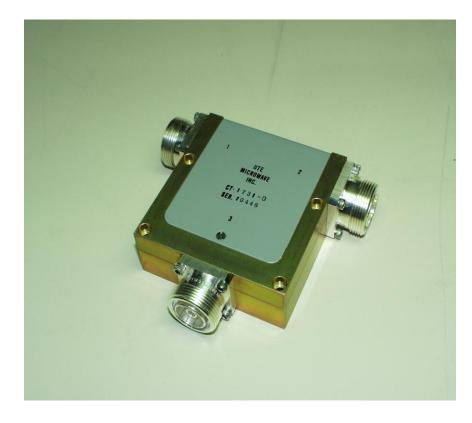
 Aluminum cold plate seems to perform better

 Thermal analysis by Jeffery Collins, ANL



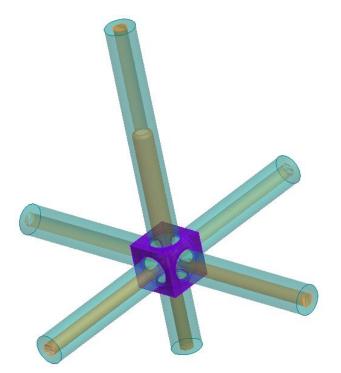
## **1kW Circulator Procurement and Test**

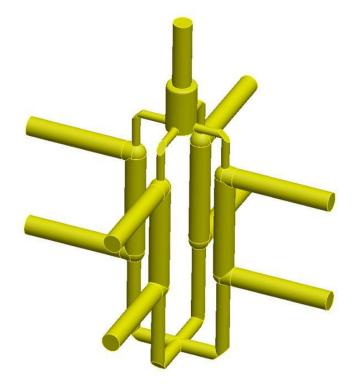
- Four circulators were purchased from UTE Microwave
- Will be used to provide amplifier isolation on the ¼-wave combiner
- One circulator has been tested under power and met advertised specifications at 1kW power level



**Design of Quarter-Wave 4-Way Combiner** 

Two combiner types were chosen for initial tests:

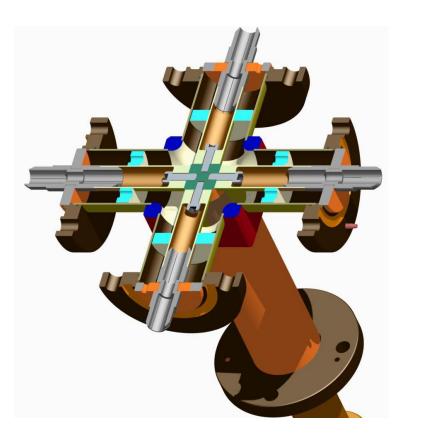




# Standard quarter-wave coaxial combiner

**Gysel Combiner** 

#### **Design of Prototype Quarter-Wave 4-Way Combiner**





- Constructed with 1-5/8" EIA standard coaxial components
- Utilizes sliding shorting plunger for tuning

#### **Conclusions From Initial Test Results**

 The <u>MRF6VP41KHR6</u> device is a possible candidate for the APS solid-state amplifier project.

 The existing APS 90°F de-ionized water system could be used to cool the amplifiers.

• Carrier + Cold Plate construction has minimal thermal impact

 Passive components and circuit board must be made more robust for continuous CW output at 1kW.



## Plan for Remainder of FY10

- 1. Investigate the possibility of maintaining at least 60% efficiency over 6dB range of output power by varying drain voltage:
  - → Test carrier amplifiers for efficiency at varying drain voltages .....Look into possible MRF6VP41KHR6 destructive parasitic oscillation?
- Demonstrate successful combined-amplifier operation at 4kW output and evaluate the system on the following criteria:
   → Overall efficiency, ac line to rf output
  - $\rightarrow$  Performance of combiner compared to EM model
- 3. Begin rf circuit design for APS 352-MHz pre-driver, driver, and 1kW amplifier boards:
  - → Investigate NXP BLF578 transistor?
- 4. Build and test 4-way Gysel combiner

The efforts and contributions of the following colleagues made this work possible:

- → Branislav Brajuskovic Mechanical Engineer, ANL
- → Jeffery Collins Mechanical Engineer, ANL
- → Leonard Morrison Mechanical Engineer, ANL
- → Geoff Waldschmidt Electrical Engineer, ANL